(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
22 February 2007 (22.02.2007)

PCT

(10) International Publication Number
WO 2007/021540 A3

(51) International Patent Classification:
G03F 7/40 (2006.01) *H01L 21/311* (2006.01)
H01L 21/027 (2006.01) *H01L 21/3213* (2006.01)

(21) International Application Number:
PCT/US2006/030028

(22) International Filing Date: 1 August 2006 (01.08.2006)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/208,098 18 August 2005 (18.08.2005) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

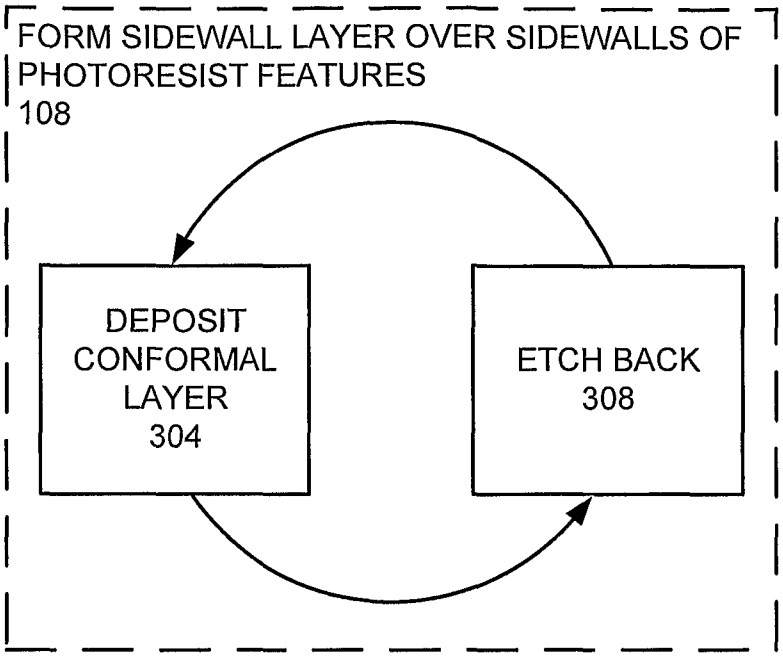
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
21 December 2007

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: ETCH FEATURES WITH REDUCED LINE EDGE ROUGHNESS



(57) Abstract: A method for forming a feature in a layer with reduced line edge roughening is provided. A photoresist layer is formed over the layer. The photoresist layer is patterned to form photoresist features with photoresist sidewalls. A sidewall layer with a thickness less than 100 nm is formed over the sidewalls of the photoresist features by performing for a plurality of cycles. Each cycle comprises depositing a layer on the photoresist layer wherein the deposited layer has a thickness between a monolayer to 20 nm. Features are etched into the layer through the photoresist features. The photoresist layer and sidewall layer are stripped.

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